

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

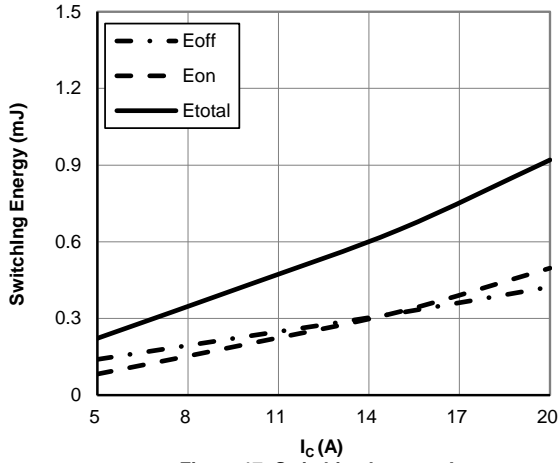


Figure 17: Switching Loss vs. I_C
($T_j=175^\circ\text{C}$, $V_{GE}=15\text{V}$, $V_{CE}=400\text{V}$, $R_g=30\Omega$)

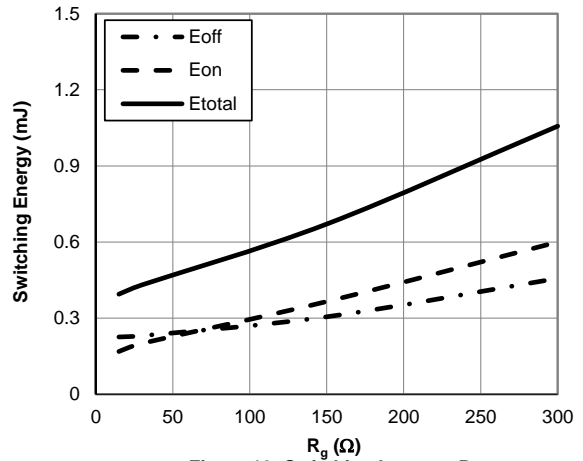


Figure 18: Switching Loss vs. R_g
($T_j=175^\circ\text{C}$, $V_{GE}=15\text{V}$, $V_{CE}=400\text{V}$, $I_C=10\text{A}$)

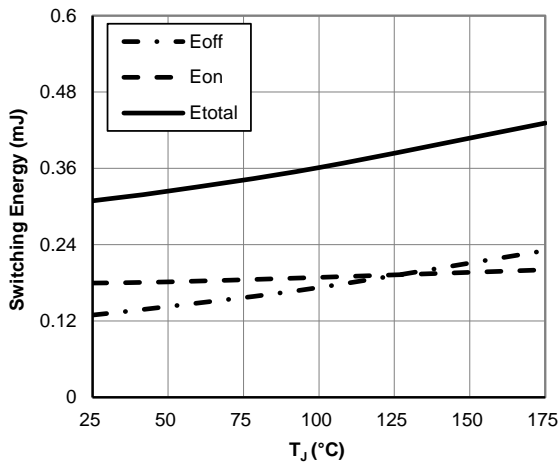


Figure 19: Switching Loss vs. T_j
($V_{GE}=15\text{V}$, $V_{CE}=400\text{V}$, $I_C=10\text{A}$, $R_g=30\Omega$)

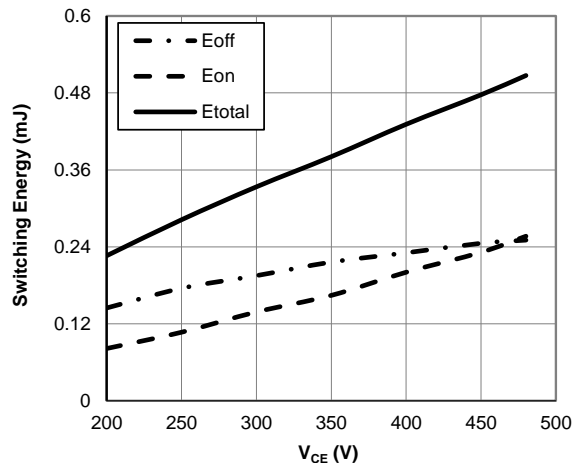


Figure 20: Switching Loss vs. V_{CE}
($T_j=175^\circ\text{C}$, $V_{GE}=15\text{V}$, $I_C=10\text{A}$, $R_g=30\Omega$)

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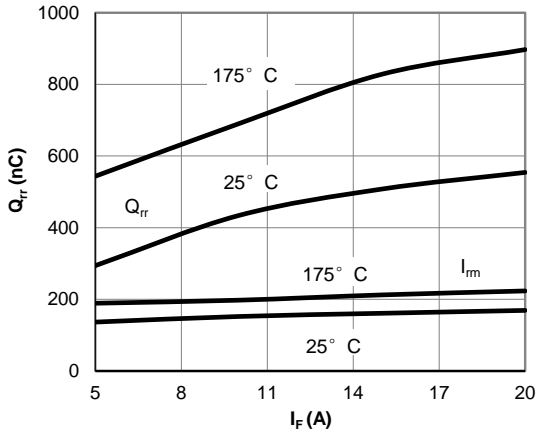


Figure 21: Diode Reverse Recovery Charge and Peak Current vs. Conduction Current
($V_{GE}=15V, V_{CE}=400V, di/dt=200A/\mu s$)

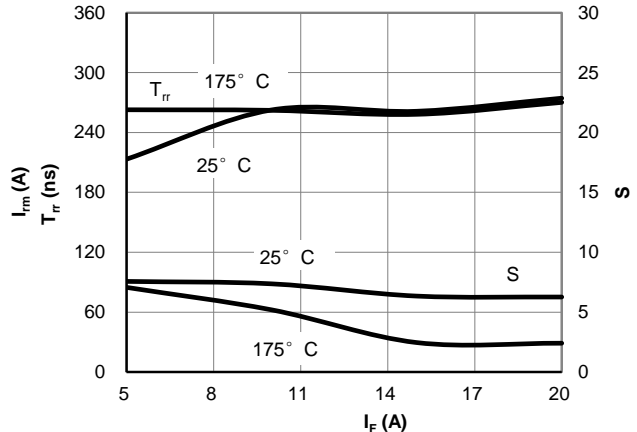


Figure 22: Diode Reverse Recovery Time and Softness Factor vs. Conduction Current
($V_{GE}=15V, V_{CE}=400V, di/dt=200A/\mu s$)

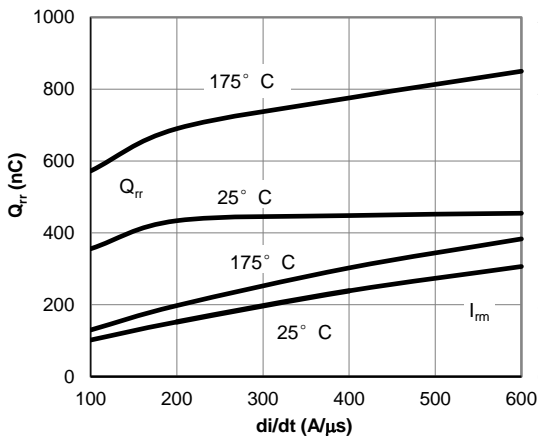


Figure 23: Diode Reverse Recovery Charge and Peak Current vs. di/dt
($V_{GE}=15V, V_{CE}=400V, I_F=10A$)

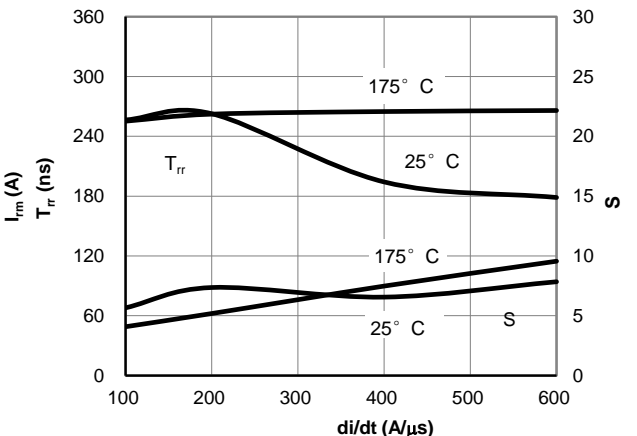


Figure 24: Diode Reverse Recovery Time and Softness Factor vs. di/dt
($V_{GE}=15V, V_{CE}=400V, I_F=10A$)

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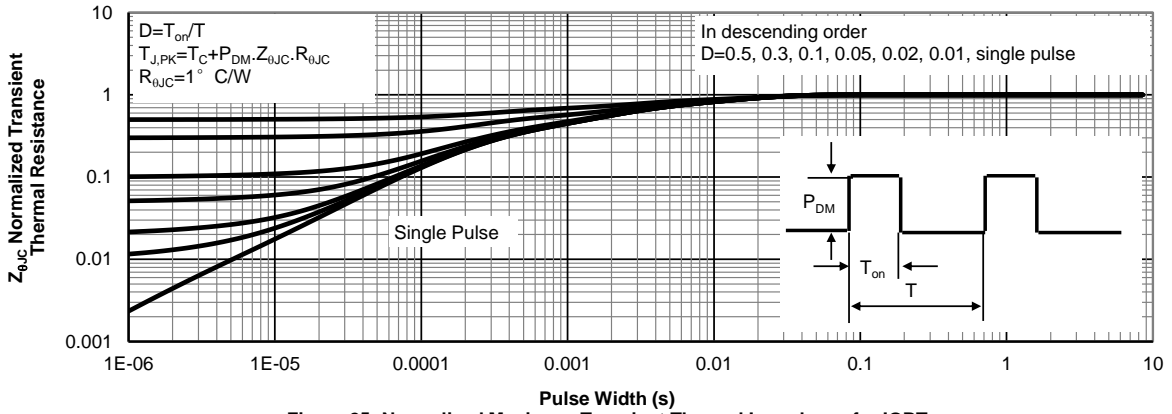


Figure 25: Normalized Maximum Transient Thermal Impedance for IGBT

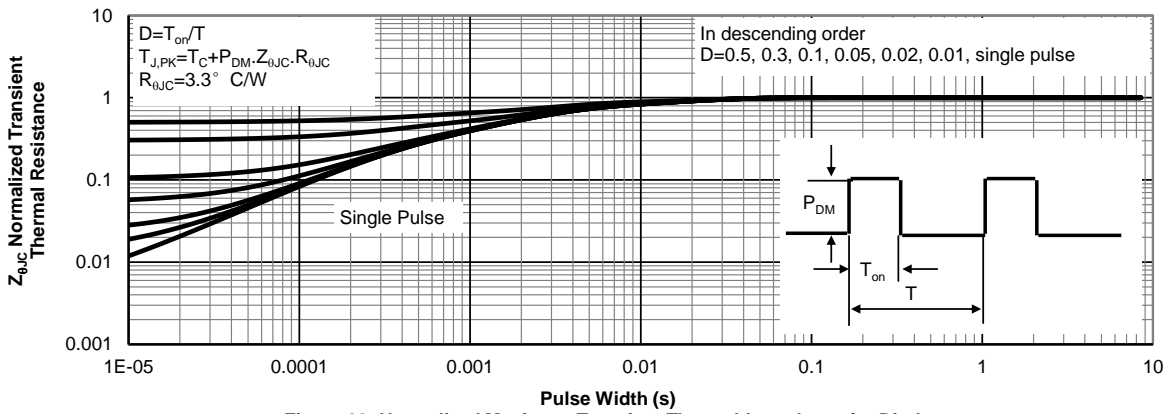


Figure 26: Normalized Maximum Transient Thermal Impedance for Diode

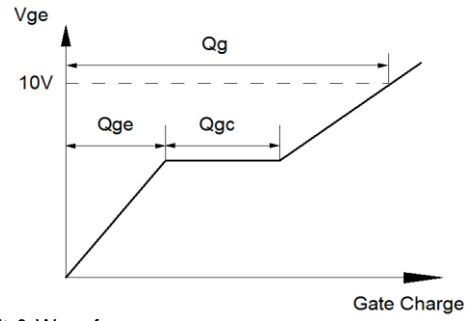
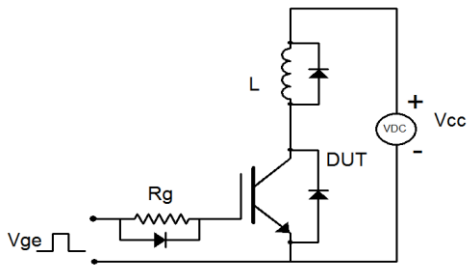


Figure A: Gate Charge Test Circuit & Waveforms

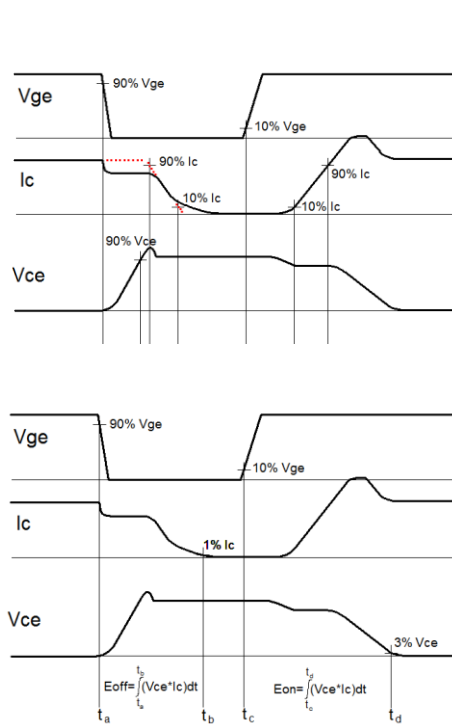
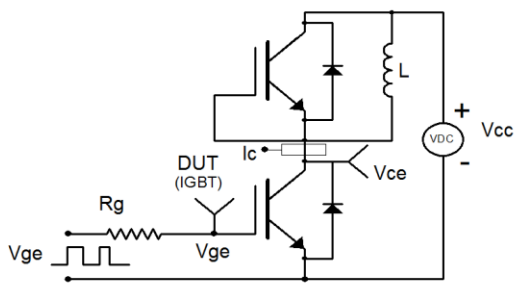


Figure B: Inductive Switching Test Circuit & Waveforms

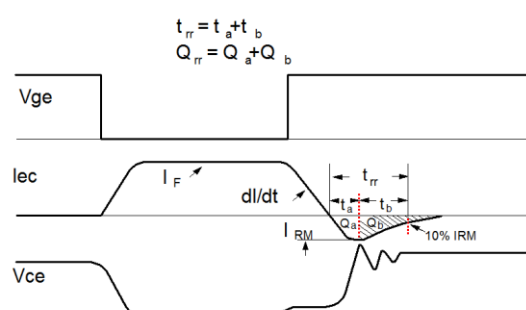
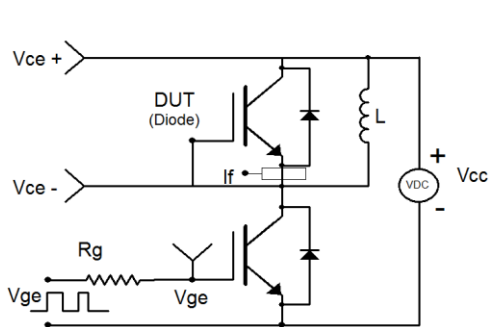


Figure C: Diode Recovery Test Circuit & Waveforms